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To

T. Miccolis Department

Code 300.1

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K. Sahu Ks\_\_\_\_

7809

Subject

Radiation Report on AD524 SMEX Common Buy Part No. 5962-8853901EA Control No. 1665 Interoffice Memorandum

PPM-92-0069

Date

Feb. 18, 1992

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731-8954

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A radiation evaluation was performed on AD524 to determine the total dose tolerance of these parts. A brief summary of the test results is provided below. For detailed information, refer to Tables I through IV and Figure 1.

The total dose testing was performed using a cobalt-60 gamma ray source. During the radiation testing, eight parts were irradiated under bias (see Figure 1 for bias configuration), and two parts were used as control samples. The total dose radiation steps were 10, 25, 50, 75, and 100 krads\*. After 100 krads, the parts were annealed at +25°C for 168 hours with measurements taken after 24 hours and 168 hours. The dose rate was between 0.3 and 5.3 krads/hour, depending on the total dose level (see Table II for radiation schedule). After each radiation exposure and annealing treatment, the parts were electrically tested @ +25°C according to the test conditions and the specification limits listed in Table III.

All irradiated parts passed all electrical measurements through 10 krads of exposure with the exception of one part which marginally exceeded the specification limit of 35 nA for the IOS parameter. Upon further irradiation to 25 krads, all of the parts exceeded the specified limits of 50 nA for +Ibias and -Thias with readings as high as 300 nA. In addition, five parts exceeded the limits for IOS, VosOut and VosIn. These parameters had readings up to 270 nA for IOS, -12 mV for VosOut (limit = -3mV), and -230 uV for VosIn (limit = 100 uV). Upon further irradiation to 100 krads, these parameters continued to degrade with the most significant degradation for +Ibias and -Ibias. These two parameters had readings up to 800 nA. Some recovery was observed after annealing the parts for 168 hours; however, all of the parts still exceeded the limits for at least one of the previously mentioned parameters. Table IV provides the mean and standard deviation values for each parameter after different irradiation exposures and annealing steps.

Any further details about this evaluation can be obtained upon request. If you have any questions, please call me at (301) 731-8954.

<sup>\*</sup>In this report, the term "rads" is used as an abbreviation for rads (Si).

## TABLE I. Part Information

Generic Part Number: 1

and the community of the control of

AD524

SMEX Common Buy

Part Number:

5962-8853901EA

SMEX Common Buy

Control Number:

1665

Charge Number:

C90105

Manufacturer:

Analog Devices

Lot Date Code:

9004

Quantity Tested:

10

Serial Numbers of

Radiation Samples:

502, 503, 504, 505, 506, 507, 508, 509

Serial Numbers of

Control Samples:

500, 501

Part Function:

PRECISION INSTRUMENTATION AMPLIFIER

WITH TRI-STATE OUTPUTS

Part Technology:

MONOLITHIC SILICON

Package Style:

16 pin DIP

Test Engineer:

K. Longworth

TABLE II. Radiation Schedule for AD524

EVENT	DATE		
1) Ir	nitial (Pre-Irradiation) Electrical Measurements	01/01/92	
-	0-KRAD IRRADIATION (500 rads/hour) OST 10-KRAD ELECTRICAL MEASUREMENT	01/13/92 01/14/92	
	5-KRAD IRRADIATION (730 rads/hour) OST 25-KRAD ELECTRICAL MEASUREMENT	01/14/92 01/15/92	
•	0-KRAD IRRADIATION (1250 rads/hour) OST 50-KRAD ELECTRICAL MEASUREMENT	01/15/92 01/16/92	
,	5-KRAD IRRADIATION (1250 rads/hour) OST 75-KRAD ELECTRICAL MEASUREMENT	01/16/92 01/17/92	
•	00-KRAD IRRADIATION (250 rads/hour) OST 100-KRAD ELECTRICAL MEASUREMENT	01/17/92 01/21/92	
	4 HOURS ANNEALING AT +25°C OST 24-HOURS ELECTRICAL MEASUREMENT	01/21/92 01/22/92	
•	68 HOURS ANNEALING AT +25°C OST 168-HOURS ELECTRICAL MEASUREMENT	01/21/92 01/28/92	

- Notes: All electrical measurements were performed off-site at +25°C.
  - All parts were radiated under bias at the cobalt-60 gamma ray facility at GSFC.
  - Annealing was performed under bias.

Table III. Electrical Characteristics of AD524

TEST NAME	TEST CONDITIONS	LOWER LIMIT	UPPER LIMIT	UNITS
GE1	$G = 1$ , $Vo = \pm 10 V$	~0. <b>0</b> 5	+0.05	* *
GE10	$G = 10$ , $Vo = \pm 10 \text{ V}$	-0.25	+0.25	ون مور مور
GE100	$G = 100$ , $Vo = \pm 10 V$	-0.50	+0.50	*
GE1000	$G = 1000$ , $Vo = \pm 10 V$			*
VosOut	Vin = 0 V	-3.0	+3.0	mV
VosIn	Vin = 0 V	-100	+100	u♥
+PSRR1	G = 1	75		đВ
+PSRR10	G = 10	95		đВ
+PSRR100	G = 100	105		đВ
+PSRR1000	G = 1000	115		đВ
-PSRR1	G = 10	75		đВ
-PSRR10	G = 10	95		đВ
-PSRR100	G = 100	105		dΒ
-PSRR1000	G = 1000	115		đВ
+Ibias	G = 1	-50	+50	nA
-Ibias	G = 1	-50	+50	nA
Ios	Iio = (Ib+)-(Ib-), G=1		+35	nA
CMRR1	G = 1, $Vin = 0$ to 10			dB
CMRR10	G = 10, $Vin = 0$ to 10			ďВ
CMRR100	G = 100, $Vin = 0$ to $10$			dB
CMRR1000	G = 1000, Vin = 0 to 10	V 110		đВ
+Iq	G = 1		5.0	mA
-Iq	G = 1	~~~= ***	5.0	mΑ

TABLE IV: Summary of Electrical Measurements After Total Dose Exposures and Annealing for AD524 1/, 2/, 3/

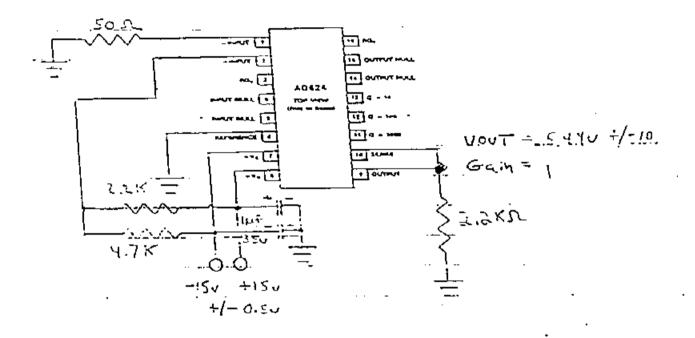
		•														Anneal		
			·	[		Total	Total Dose Exposure (TDE) (krads)								<del></del>			
		Spec Limits		0		10	10		25	50		7.5		100		168 hours		
		e 25°C		(Pre-R	Pre-Rad)				1									
Parameters		min	max	mean	sđ	mean	#d	mean	sd	mean	sđ.	mean	sđ	леал	ba	mean	sđ.	
	*	0	0.05	0.004	0.004	0.004	0.004	0.004	0.003	0_004	0.003	0.004	0.003	0.004	0.504	0.004	0.003	
	*	0	0.25	0.013	0.015	0.015	0.520	0,014	0.019	0.013	0.015	0.013	0.015	0.013	0.015	0.013	<del></del> -	
GainBrr X100	*	0	0.50	0,087	0.051	0.101	0.046	0,104	0.042	0.095	0.043	0.094	0.043	0.105	0.057	0.109	0.039	
GainBrr X1000		0	2.00	0.105	0.079	0.172	0.089	0,156	0.123	0.160	0.108	0.199	0.159	0.229	0.200	0.309	0.276	
Vos0ut	γπ.V	0	3.00	0,17	0.17	0.68	0.84	4.22	5.17	4.14	3.95	4.44	4.08	4.70	4.08	3.13	2.50	
VosIn	u <b>v</b>	0	100	14.0	20.8	26,9	29.7	104.8	118.5	97.3	90.2	101.3	97.5	100.7	97.2	65.3	62.7	
+PSRR X1	₫B	75	-	9.5 25	18.0	106-0	12.4	106.6	9.8	91.9	14.6	93.9	17.0	94.9	16.9	94.4	17.4	
+PSRR X10	dB	95	-	106.2	17.9	124.6	12.1	123.9	11.2	109.2	17.1	114.7	23.7	109.5	19.7	107.2	16-7	
*PSRR X100	dB	105	-	127.1	<b>19</b> . 8	139.9	11.2	130.7	5.9	124.1	21.1	123.0	22.8	119.9	19.0	120.2	19.1	
+PSRR X1000	đВ	115	-	126.6	21.9	139.0	8.6	138.5	12,6	122.3	17.9	117.4	16.6	119.1	13.8	115.3	16.4	
-PSRR X1	dВ	75	_	72,6	10.6	82.7	5.4	63.2	5.2	74.1	11.1	73.9	11.1	74.2	11.4	74.5	11.5	
-PSRR X10	dВ	9.5	-	90.3	12.9	102.5	5.4	102.8	5.0	91.7	13.5	91.9	12.5	91.4	13.3	91.8	13.4	
-PSRR X100	dВ	105	<b>-</b> .:	106.8	14.9	122.3	6.0	121.4	4.5	109.9	16.1	108.9	15.9	108.9	15.5	109.0	17.3	
-psrm x1000	dВ	115		118.2	16.9	134.6	5.6	135.1	8.1	119.7	18.1	118.3	15.4	1,26.9	29.7	116.5	<del></del>	
+Ibias	nA	0	50.0	2.11	3.39	1895	7.08	186.9	59.3	221.7	82.0	272.2	99.8	435.5	151.8	371.3	113.9	
-Ibias	nA	٥	50.0	9,62	5.05	15.3	17.0	151.6	118.2	191.5	91.0	235.1	111.0	372.1	190.7	334,5	141.5 67.2	
Tos	πA	a	35.0	3,59	2.94	14.0	17.7	B7.9	110.7	86.4	90.5	92.4	95.0	99.6	105.2	66.3	11.5	
CMRR X1	dВ	70	-	80.9	12.5	91.0	6.0	90.3	5.5	80,1	11.9	79.8	11.8	79.8	11.6	79.3 97.1	13.8	
CMRR X10	dВ	9.0		98.8	14.6	111.1	6.1	110.4	5.8	97,9	14.1	97.7	14.0	97.7	13.6	115.5	16.7	
CMRR X100	dB	100		119.9	20.9	133.1	8.8	134.0	10.9	117.7	18.1	115.0	18.1	117.3 129.9	19.0	131.6	22.3	
CMRR X1000	dB	110		130.4	18.1	150.6	14.2	150.6	15.3	120.9	19.6	133.3	22,2	2.91	0.47	2.94	0.47	
+Iq	πA	a	5.0	3,16	0.50	3.53		3.38	0.26	2,98	0.48	2.95	0.48		0.47	2.95	0.47	
-Iq	πλ	G	5.0	3.19°	0.50	3.55	0.26	3.39	0.27	2.98	0.46	2.96	0.48	2.92	0.47	150 Sec. 10 100	0.47	

<sup>1/</sup> These statistics do not include the control samples which remained constant throughout testing.

<sup>2/</sup> The statistics for the post 24 hour annealing steps are available upon request.

<sup>3/</sup> During the initial electrical measurements S/N 503 was marginally below the specification limits for -PSRR at Gain = 1X and 10X. These parameters were disregarded for S/N 503 throughout testing.

Figure 1. Radiation Bias Circuit for AD524



NOTE: ALL RESISTORS ARE 10% 14 Water